



INFORMATION DISCLOSURE CITATION PTO-1449	Atty. Docket No. 970813	Serial No. 09/921,250
	Applicant(s): Y. INOUE et al.	OCT 25 2000
	Filing Date: August 29, 1997	GROUP 1700

U.S. PATENT DOCUMENTS

Examiner Initial	Document No.	Name	Date	Class	Subclass	Filing Date (If appropriate)
ggg	AA 6,071,807	Watanabe et al.	06/2000			
	AB 5,087,589	Chapman et al.	02/1992			
	AC 5,341,026	Harada et al.	08/1994			
	AD 5,514,910	Koyama	05/1996			
	AE 5,607,880	Suzuki et al.	03/1997			
	AF 5,702,568	Shin et al.	12/1997			
	AG 5,314,834	Mazure et al.	05/1994			
	AH 5,665,845	Allman	09/1997			
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	Document No.	Date	Country	Translation (Yes/No)
ggg	AJ 2-235358	09/18/90	Japan	—
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INFORMATION DISCLOSURE CITATION PTO-1449	Atty. Docket No. 970813	Serial No. 09/921,250 US, 9/21,250 10/17/2000 RECEIVED
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gpg	AL	Wang et al. , "A Study of Plasma Treatments on Siloxane SOB," IEEE VMIC Conference, June 7-8, 1994, pp. 101-107.
	AM	Chiang et al., "Defects Study on Spin on Glass Planarization Technology, IEEE VMIC Conference, June 15-16, 1987, pp. 404-412.
	AN	Lai-Juh Chen, et al., "Fluorine-Implanted Treatment (FIT) SOG for the Non-Etchback Intermetal Dielectric," IEEE VMIC Conference, June 7-8, 1994, pp. 81-86.
	AO	Moriya et al., "Modification Effects in Ion-Implanted SiO ₂ Spin-on-Glass," <u>J. Electrochem. Soc.</u> , Vol. 140, No. 5, May 1993, pp. 1442-1450.
	AP	Matsuura et al., "An Advanced Interlayer Dielectric System with Partially Converted Organic SOG Using Plasma Treatment," IEEE VMIC Conference, June 8-9, 1993, pp. 113-115.
	AQ	Ishida et al., "Mechanism for AlSiCu alloy Corrosion," <u>Jpn. J. Appl. Phys.</u> , Vol. 31 (1992), pp. 2045-2048.
	AR	Doki et al., "Moisture-Blocking Mechanism of ECR-Plasma," IEEE VMIC Conference, June 7-8, 1994, pp. 235-139.
	AS	Shimokawa et al., "Suppression of MOSFET hot carrier degradation by P-SiO underLayer," <u>The Institute of Electronics, Information and Communication Engineers</u> , Technical Report of IEICE, SDM92-133 (1992-12), pp. 89-94.
gpg	AT	Murase et al., "Dielectric Constant of Silicon Dioxide Deposited by Atmospheric-Pressure Chemical Vapor Deposition Using Tetraethylorthosilicate and Ozone," <u>Jpn. J. Appl. Phys.</u> , Vol. 33 (1994), pp. 1385-1389.

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INFORMATION
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Atty. Docket No. 970813

Serial No. 08/921,250

Applicant(s): Yasunori INOUE et al.

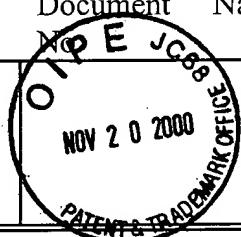
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AA
AB
AC



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OPA	AD	LITHOGRAPHY 1: OPTICAL RESIST MATERIALS AND PROCESS TECHNOLOGY, pp. 441.
OPA	AE	SILICON PROCESSING FOR THE VLSI ERA - VOLUME II; 4.4.9.1 SOG Process Intefration, pp. 232.
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